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Class	151					٠
		U.S. UT	ILITY Patent	t Application	n	
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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER	
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Kazuyuki Hiroaki (

Kazuyuki Tadat Hiroaki Okagaw Yoichiro Ouchi Masahiro Koto **APPLICANTS**

semiconductor base and its manufacturing method, and semiconductor crystal manufacturing method

ISSUING CLASSIFICATION										
ORIGINAL		, CROSS REFERENCE(S)								
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TERMINAL		DRAWINGS			CLAIMS ALLOWED		
L DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.		
☐ The term of this patent				NOTICE OF ALLOWANCE MAILED			
subsequent to (date) has been disclaimed.	(Assistant Examiner) (Date)						
The term of this patent shall not extend beyond the expiration date							
of U.S Patent. No.				ISSUE FEE			
				Amount Due	Date Paid		
	(Primary Examiner) (Date)						
☐ The terminalmonths of this patent have been disclaimed.				ISSUE BATCH NUMBER			
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